查询"2<u>SK376%</u>#ie商Field Effect Transistor Silicon N Channel MOS Type (兀MOS)

2SK3760

unit: mm

Switching Regulator Applications

- Low drain-source ON resistance: RDS (ON) = 1.7 (typ.)
- High forward transfer admittance: $|Y_{fs}| = 2.5S$ (typ.)
- Low leakage current: $IDSS = 100 \mu A (VDS = 600 V)$
- Enhancement-mode: $V_{th} = 2.0 \sim 4.0 \text{ V (V DS} = 10 \text{ V, ID} = 1 \text{ mA})$

Maximum Ratings (Ta = 25°C)

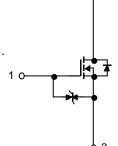
Characte	ristics	Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	600	V
Drain-gate voltage (F	$R_{GS} = 20 \text{ k}\Omega$	V_{DGR}	600	V
Gate-source voltage		V_{GSS}	±30	V
	DC (Note 1)	l _D	3.5	Α
Drain current	Pulse (t = 1 ms) (Note 1)	l _{DP}	14	
Drain power dissipati	on (Tc = 25°C)	P_{D}	60	W
Single pulse avalanc	he energy (Note 2)	E _{AS}	6.3	mJ
Avalanche current		l _{AR}	3.5	Α
Repetitive avalanche	energy (Note 3)	E _{AR}	6	mJ
Channel temperature)	T _{ch}	150	°C
Storage temperature	range	T _{stg}	-55~150	°C

39 max 15.6 max	2.52 1 2	3	0.45	
3.		n(HEAT S rce	INK)	
JEDE	С	TO-2	220AB	
JEITA		SC-4		

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	2.08	°C/W
Thermal resistance, channel to ambient	R _{th (ch-a)}	83.3	°C/W

Weight: 2.0g(typ.)



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- Note 1: Please use devices on conditions that the channel temperature is below 150°C.
- Note 2: $V_{DD} = 90 \text{ V}$, $T_{ch} = 25^{\circ}\text{C}$ (initial), L = 0.9 mH, $I_{AR} = 3.5 \text{ A}$, $R_G = 25 \Omega$
- Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution.



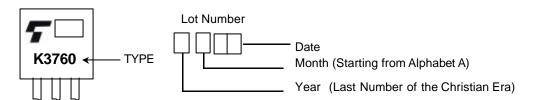
Erectrica Character istics (Ta = 25°C)

Char	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		lgss	$V_{GS} = \pm 25 V, V_{DS} = 0 V$	_	_	±10	μΑ
Gate-source breakdown voltage		V (BR) GSS	$I_D = \pm 10 \ \mu A, \ V_{GS} = 0 \ V$	±30	_	_	V
Drain cut-off current		I _{DSS}	$V_{DS} = 600 \text{ V}, V_{GS} = 0 \text{ V}$	_	_	100	μΑ
Drain-source bre	akdown voltage	V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	600	_	_	V
Gate threshold v	oltage	V_{th}	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	2.0	_	4.0	V
Drain-source ON	l resistance	R _{DS (ON)}	$V_{GS} = 10 \text{ V}, I_D = 1.8 \text{ A}$	_	1.7	2.2	Ω
Forward transfer	admittance	Y _{fs}	$V_{DS} = 10 \text{ V}, I_D = 1.8 \text{ A}$	0.7	2.5	_	S
Input capacitance		C _{iss}		_	550		
Reverse transfer capacitance		C _{rss}	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	6	_	pF
Output capacitance		C _{oss}			60		
Switching time	Rise time	t _r	10 V		12		
	Turn-on time	t _{on}	$R_{L} = 111 \Omega$ $V_{DD} \approx 200 V$	_	45		20
	Fall time	t _f			13		ns
	Turn-off time	t _{off}	Duty ≦ 1%, t _w = 10 μs	_	80		
Total gate charge		Qg		_	16	_	
Gate-source charge		Q _{gs}	$V_{DD} \simeq 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 3.5 \text{ A}$		10		nC
Gate-drain charge		Q _{gd}			6		

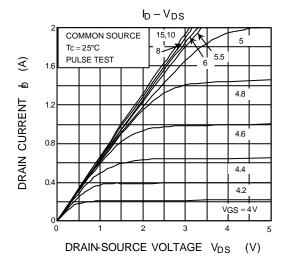
Source-Drain Ratings and Characteristics (Ta = 25°C)

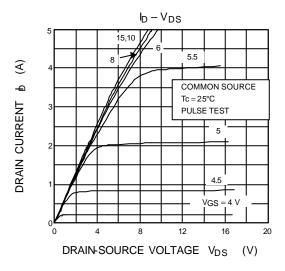
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	l _{DR}	_	_	_	3.5	А
Pulse drain reverse current (Note 1)	I _{DRP}	_	_	_	14	Α
Forward voltage (diode)	V_{DSF}	$I_{DR} = 3.5 \text{ A}, V_{GS} = 0 \text{ V}$	_		-1.7	V
Reverse recovery time	t _{rr}	$I_{DR} = 3.5 \text{ A}, V_{GS} = 0 \text{ V},$	_	1400	_	ns
Reverse recovery charge	Q _{rr}	$dI_{DR}/dt = 100 A/\mu s$		9	_	μС

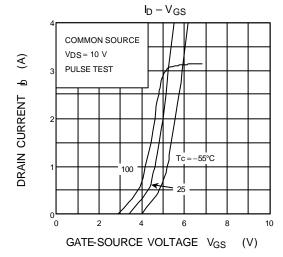
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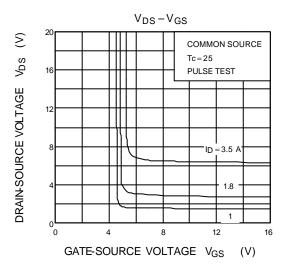


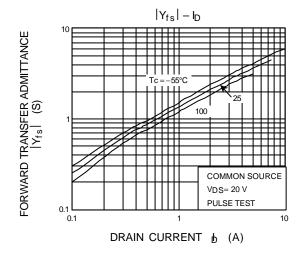
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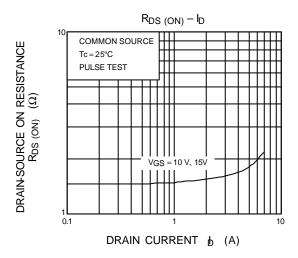




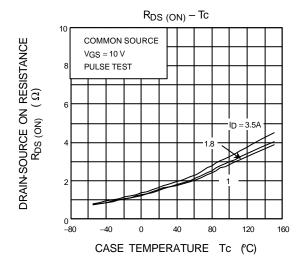


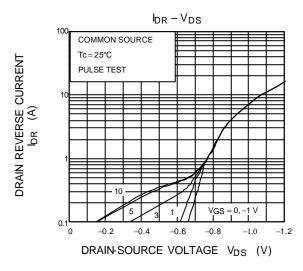




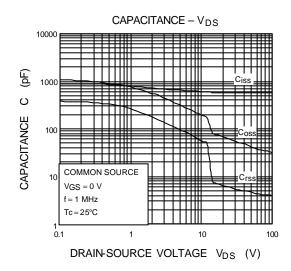


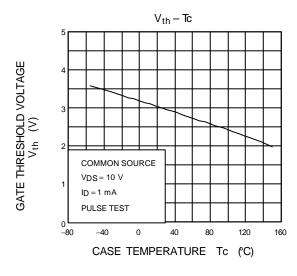


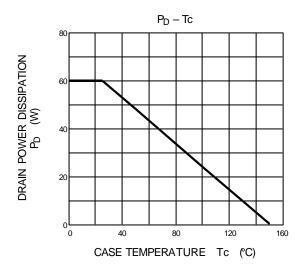


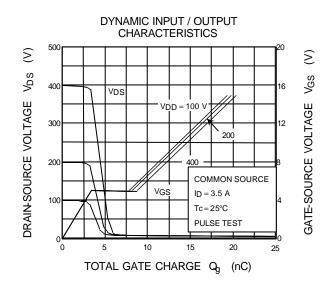


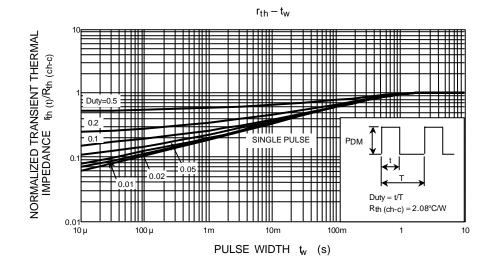
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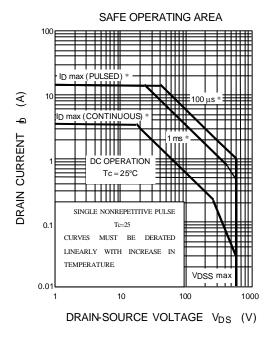


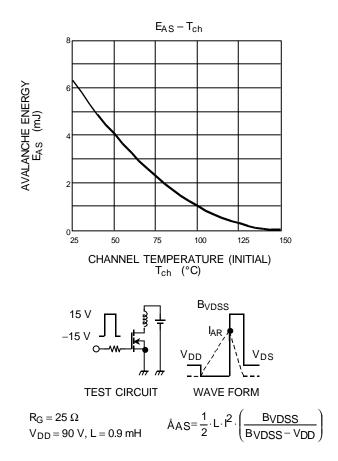












5 2004-02-26

RESTRICTIONS ON PRODUCT USE

Handbook" etc..

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